

DERWENT-ACC-NO: 1998-574564

DERWENT-WEEK: 199901

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TITLE: Multilayer interconnection structure
in semiconductor device - has condensed film between
metal wiring formed on wiring groove and porous
dielectric film

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PRIORITY-DATA: 1997JP-0059413 (March 13, 1997)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC
JP 10256363 A		September 25, 1998	N/A
006	H01L 021/768		

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
JP 10256363A	N/A	1997JP-
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INT-CL (IPC): H01L021/768

ABSTRACTED-PUB-NO: JP 10256363A

BASIC-ABSTRACT:

The structure consists of a porous dielectric film (14) made of silicon resin or polyfluoro ethylene resin formed on a silicon oxide substrate (1) via a silicon oxide film (2). An insulating film (7) made of silicon nitride is

formed on porous dielectric film.

The porous dielectric film is irradiated by laser or electron beam and wiring groove (10) corresponding to wiring pattern is formed. A metal wiring (8) is formed on wiring groove. A condensed film (6) is formed between metal wiring and dielectric film.

ADVANTAGE - Prevents absorption of gas by porous dielectric film.

CHOSEN-DRAWING: Dwg.2/2

DERWENT-CLASS: A85 L03 U11

CPI-CODES: A04-E10A; A06-A00E2; A09-A03; A11-C04E; A12-E07C; L04-C13;

EPI-CODES: U11-C05D3;

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Basic Abstract Text - ABTX (2):

The porous dielectric film is irradiated by laser or electron beam and wiring groove (10) corresponding to wiring pattern is formed. A metal wiring (8) is formed on wiring groove. A condensed film (6) is formed between metal wiring and dielectric film.